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Kind regards,

Team Nexperia

1PS76SB21; **BAT721** series

Schottky barrier diodes in small packages

Rev. 06 — 21 December 2006

Product data sheet

1. Product profile

1.1 General description

Planar Schottky barrier diodes with an integrated guard ring for stress protection. Encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package		Configuration
	NXP	JEITA	
1PS76SB21	SOD323	SC-76	single
BAT721	SOT23	-	single
BAT721A	SOT23	-	dual common anode
BAT721C	SOT23	-	dual common cathode
BAT721S	SOT23	-	dual series

1.2 Features

- Low forward voltage
- Small SMD plastic packages
- Low capacitance

1.3 Applications

- Ultra high-speed switching
- Voltage clamping
- Line termination
- Reverse polarity protection

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
I _F	forward current		-	-	200	mA
V_R	reverse voltage		-	-	40	V
V_{F}	forward voltage	$I_F = 200 \text{ mA}$	<u>[1]</u> -	-	550	mV

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



2. Pinning information

Table 3. **Pinning** Pin Description Simplified outline **Symbol** 1PS76SB21 [1] 1 cathode 1 - 2 2 anode sym001 **BAT721** 1 anode 3 2 not connected 3 cathode n.c. 006aaa144 **BAT721A** cathode (diode 1) 3 2 cathode (diode 2) 3 anode (diode 1), anode (diode 2) 006aaa439 1 2 006aaa144 **BAT721C** 1 anode (diode 1) 3 2 anode (diode 2) 3 cathode (diode 1), cathode (diode 2) 006aaa438 2 006aaa144 **BAT721S** 1 anode (diode 1) 3 2 cathode (diode 2) 3 cathode (diode 1), anode (diode 2) 006aaa437 2 1 006aaa144

[1] The marking bar indicates the cathode.

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3. Ordering information

Table 4. Ordering information

Type number	Package				
	Name	Description	Version		
1PS76SB21	SC-76	plastic surface-mounted package; 2 leads	SOD323		
BAT721	-	plastic surface-mounted package; 3 leads	SOT23		
BAT721A					
BAT721C					
BAT721S					

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
1PS76SB21	S1
BAT721	L7*
BAT721A	L8*
BAT721C	L9*
BAT721S	L0*

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V_R	reverse voltage		-	40	V
I _F	forward current		-	200	mA
I _{FSM}	non-repetitive peak forward current	half sine wave; JEDEC method; $t_p = 8.3 \text{ ms}$	-	1	Α
Tj	junction temperature		-	125	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

6. Thermal characteristics

Table 7 Thermal characteristics

Table 1.	Thermal Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	1PS76SB21		-	-	450	K/W
	BAT721		-	-	500	K/W
	BAT721A		-	-	500	K/W
	BAT721C		-	-	500	K/W
	BAT721S		-	-	500	K/W

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

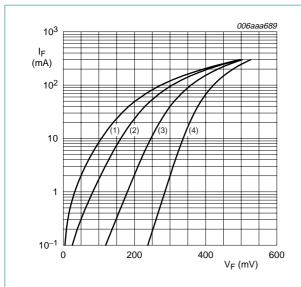
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \,^{\circ}C$ unless otherwise specified.

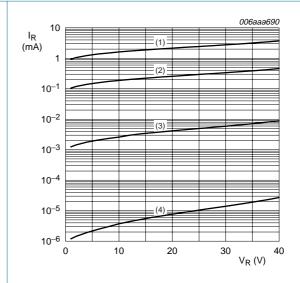
anno		•				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode)					
V _F forward vo	forward voltage	I _F = 10 mA	<u>[1]</u> _	-	300	mV
		I _F = 100 mA	<u>[1]</u> _	-	420	mV
		I _F = 200 mA	<u>[1]</u> _	-	550	mV
I _R	reverse current	V _R = 30 V	-	-	15	μΑ
		$V_R = 30 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	-	3	mA
C _d	diode capacitance	$V_R = 0 V; f = 1 MHz$	-	40	50	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$



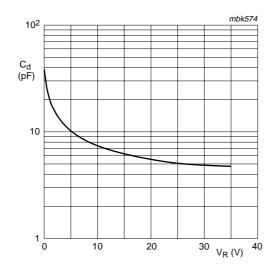
- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \,^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

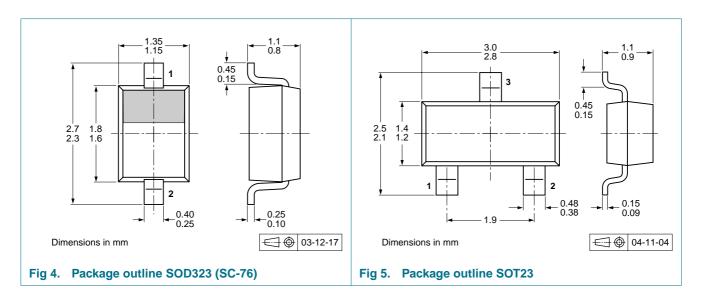
Fig 2. Reverse current as a function of reverse voltage; typical values



 $T_{amb} = 25 \,^{\circ}\text{C}$; $f = 1 \, \text{MHz}$

Fig 3. Diode capacitance as a function of reverse voltage; typical values

8. Package outline



9. Packing information

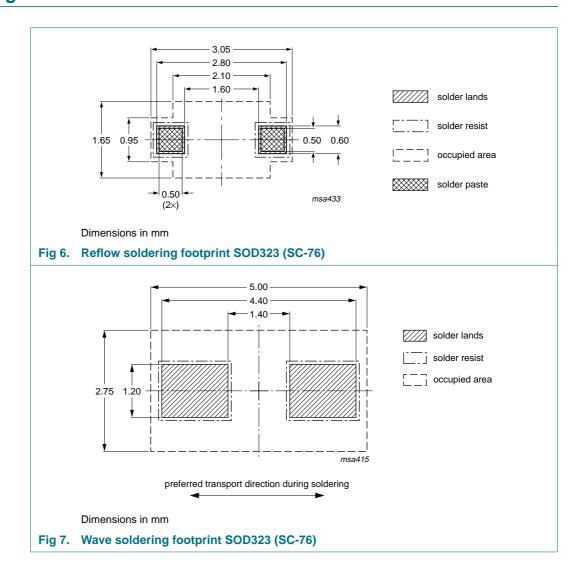
Table 9. Packing methods

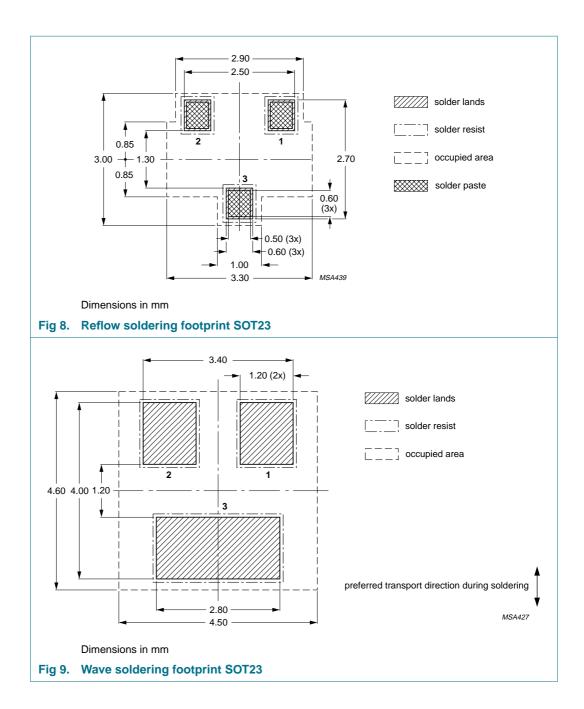
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity		
			3000	10000		
1PS76SB21	SOD323	4 mm pitch, 8 mm tape and reel	-115	-135		
BAT721	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235		
BAT721A						
BAT721C						
BAT721S						

[1] For further information and the availability of packing methods, see Section 13.

10. Soldering





11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
1PS76SB21_BAT721_SER_6	20061221	Product data sheet	-	1PS76SB21_BAT721 _SER_5			
Modifications:	 Amended Ta 	able 10 "Revision history"					
1PS76SB21_BAT721_SER_5	20061205	Product data sheet	-	BAT721_SERIES_4 1PS76SB21_3			
Modifications:	 The format of this data sheet has been redesigned to comply with the new identification. 						
	 Legal texts h 	nave been adapted to the ne	ew company name wh	ere appropriate.			
	 This data sh 1PS76SB21 	eet is a combination of data _3.	a sheets BAT721_SER	IES_4 and			
	• Table 1 "Pro	duct overview": added					
	Section 1.2 '	"Features": amended					
 <u>Section 1.3 "Applications"</u>: amended 							
	Table 2 "Quick reference data": added						
	 <u>Table 5 "Marking codes"</u>: for 1PS76SB21 amended 						
	Table 5 "Mar	king codes": enhanced table	le note section				
	 Table 6 "Lim 	iting values": indication per	diode added				
	• Table 6 "Lim	iting values": for 1PS76SB2	21 I _{FSM} condition amer	nded			
	 Table 6 "Lim 	iting values": T _{amb} ambient	temperature added				
	Table 7 "The	ermal characteristics": indica	ation per diode added				
	 <u>Table 7</u>: R_{th(j} 	_{j-a)} thermal resistance from	junction to ambient co	ndition amended			
	 Table 8 "Cha 	aracteristics": indication per	diode added				
	 Table 8 "Cha 	aracteristics": reference to T	able note 1 amended				
		1PS76SB21 C _d minimum va	alue changed to typical	l value			
		d 2: amended					
		d 5: superseded by minimize	ed package outlines				
		acking information": added					
	Section 10 "	Soldering": added					
	Section 12 "I	Legal information": updated					
BAT721_SERIES_4	20040315	Product specification	-	BAT721_SERIES_3			
1PS76SB21_3	20040126	Product specification	-	1PS76SB21_2			

1PS76SB21; BAT721 series

Schottky barrier diodes in small packages

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors

1PS76SB21; BAT721 series

Schottky barrier diodes in small packages

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